TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

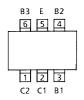
TA4100F

UHF VHF RF, MIX Application

Features

- High f_T. (f_T = 5 GHz)
- Differential circuit is composed of 3 transistors.

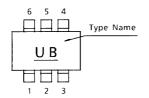
Pin Assignment (top view)

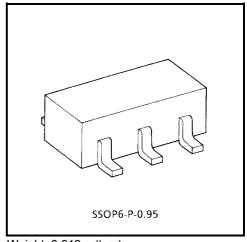


C ... COLLECTOR

B ... BASE E ... EMITTER

Marking





Weight: 0.013 g (typ.)

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Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit	
Collector-base voltage	V_{CBO}	10	V	
Collector-emitter voltage	V _{CEO}	5	V	
Collector current	Ic	15 (Note 1)	mA	
		30 (Note 2)		
Total power dissipation	P _D (Note3)	300	mW	
Operating temperature	T _{opr}	-40~85	°C	
Storage temperature range	T _{stg}	-55~125	°C	

Note 1: Q1, Q2

Note 2: Q3

Note 3: When mounted on the glass epoxy board of 2.5 $\text{cm}^2 \times 1.6 \text{ t}$

Electrical Characteristics (Ta = 25°C)

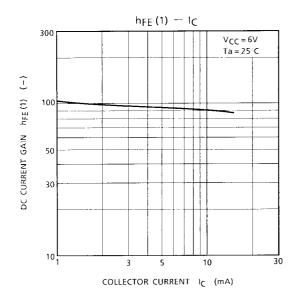
Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector-emitter voltage	V _{CEO} (1)	_	$I_{C1} = 1.0 \text{ mA},$ $(I_{B3} = 1 \text{ mA})$ (Note 4)	5	-	1	V
	V _{CEO} (2)	_	$I_{C2} = 1.0 \text{ mA},$ $(I_{B3} = 1 \text{ mA})$ (Note 5)	5	-	1	
	V _{CEO} (3)	_	$I_{B1} (I_{C3} = 1.0 \text{ mA})$ (Note 6)	5	_	_	
DC Current gain	h _{FE} (1)	_	$V_{C1} = 6 \text{ V}, I_{C1} = 5 \text{ mA}, (I_{B3} = 1 \text{ mA})$ (Note 4)	50	100	160	_
	h _{FE} (2)	_	$V_{C2} = 6 \text{ V}, I_{C1} = 5 \text{ mA}, (I_{B3} = 1 \text{ mA})$ (Note 5)	50	100	160	
	h _{FE} (3)	_	$V_{B1} (V_{C3}) = 6 V,$ $I_{B1} (I_{C3}) = 10 \text{ mA}$ (Note 6)	70	140	250	
Transition Frequency	f _T (1)	_	$V_{C1} = 6 \text{ V}, I_{C1} = 5 \text{ mA}, (I_{B3} = 1 \text{ mA})$ (Note 4)	3.5	5.0	7.0	
	f _T (2)		V _{C2} = 6 V, I _{C2} = 5 mA, (I _{B3} = 1 mA) (Note 5)	3.5	5.0	7.0	GHz
	f _T (3)		$V_{B1} (V_{C3}) = 4 V,$ $I_{B1} (I_{C3}) = 10 \text{ mA}$ (Note 6)	3.5	5.0	7.0	

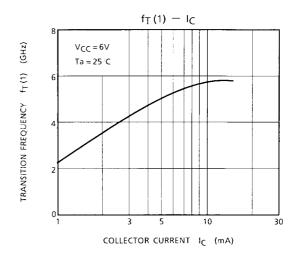
Note 4: Characteristics of Q1

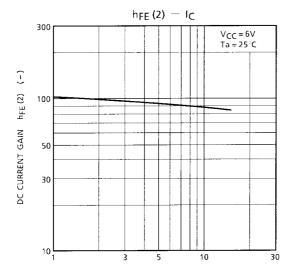
Note 5: Characteristics of Q2

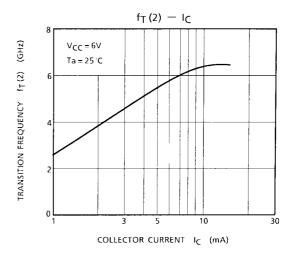
Note 6: Characteristics of Q3

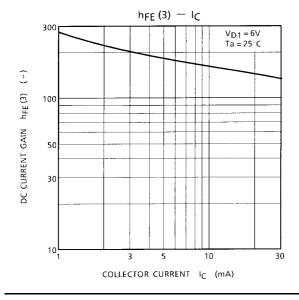
Equivalent Circuit

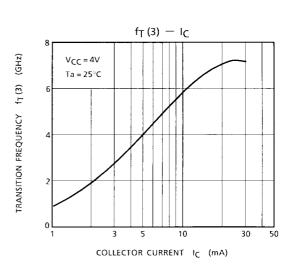








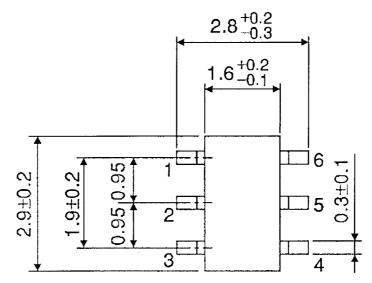


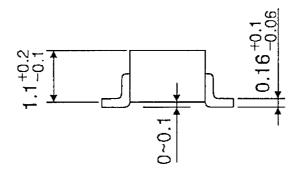




Package Dimensions

SSOP6-P-0.95 Unit: mm





Weight: 0.013g (Typ.)